



**Advanced Power
Electronics Corp.**

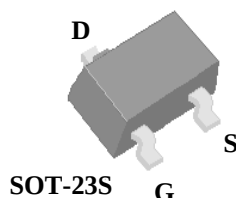
AP2325GEN

Halogen-Free Product

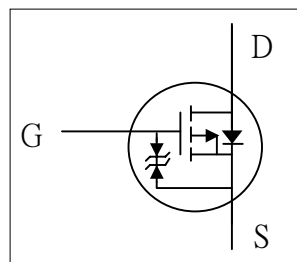
P-CHANNEL ENHANCEMENT MODE

POWER MOSFET

- ▼ Capable of 2.5V Gate Drive
- ▼ Small Package Outline
- ▼ Surface Mount Device
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	-20V
$R_{DS(ON)}$	90m Ω
I_D	- 3A



Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The SOT-23S package is widely preferred for commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D@T_A=25^\circ\text{C}$	Drain Current ³ , V_{GS} @ 4.5V	-3	A
$I_D@T_A=70^\circ\text{C}$	Drain Current ³ , V_{GS} @ 4.5V	-2.4	A
I_{DM}	Pulsed Drain Current ¹	-12	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	1.25	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	100	$^\circ\text{C}/\text{W}$



AP2325GEN

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-3A	-	70	90	mΩ
		V _{GS} =-2.5V, I _D =-2A	-	95	130	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-0.3	-0.7	-1	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	-	8	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±12V, V _{DS} =0V	-	-	±30	uA
Q _g	Total Gate Charge	I _D =-3A	-	6	9.6	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-10V	-	1	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	1.7	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-10V	-	7	-	ns
t _r	Rise Time	I _D =-1A	-	16	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	21	-	ns
t _f	Fall Time	V _{GS} =-5V	-	5	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	520	830	pF
C _{oss}	Output Capacitance	V _{DS} =-10V	-	70		pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	55	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1.2A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-3A, V _{GS} =0V,	-	15	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	7	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤ 10s ; 300°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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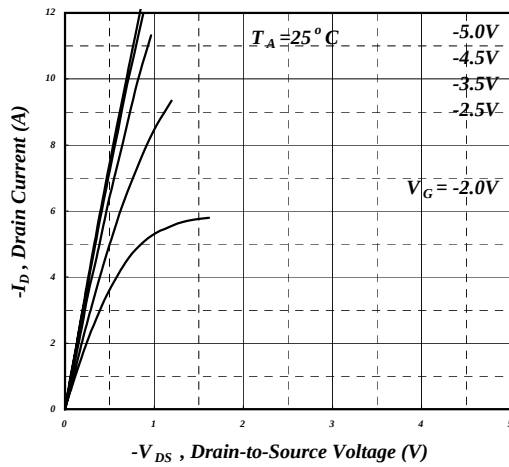


Fig 1. Typical Output Characteristics

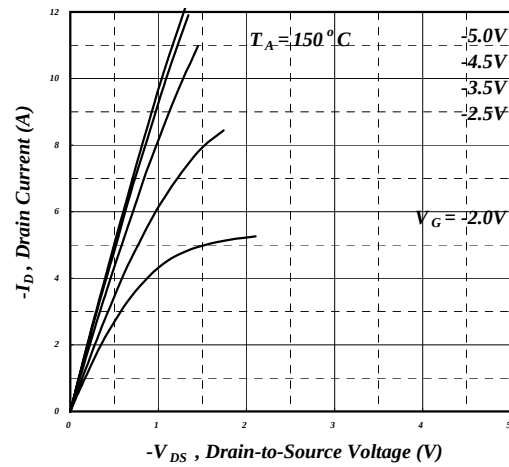


Fig 2. Typical Output Characteristics

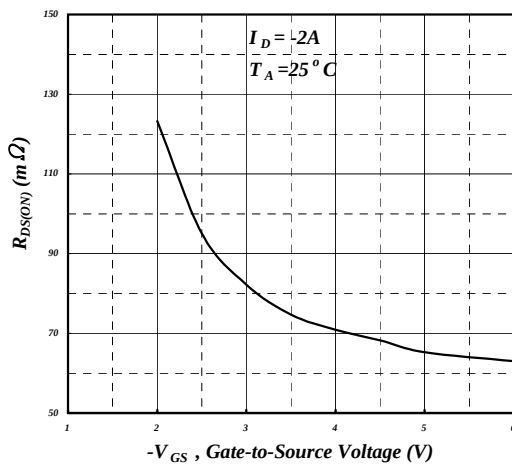


Fig 3. On-Resistance v.s. Gate Voltage

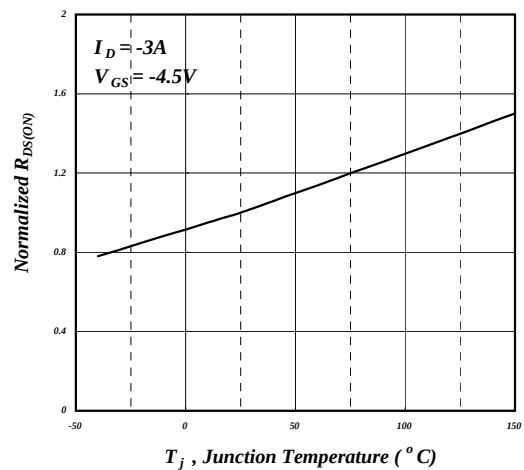


Fig 4. Normalized On-Resistance v.s. Junction Temperature

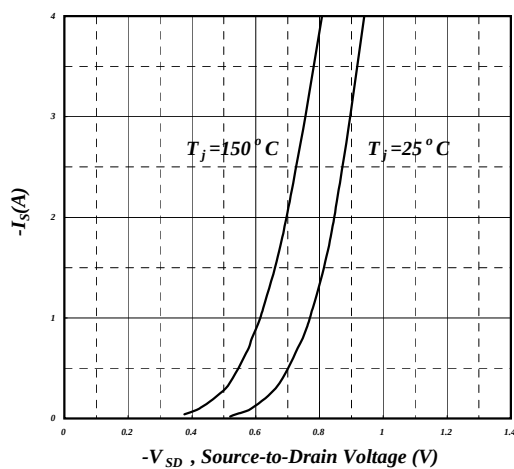


Fig 5. Forward Characteristic of Reverse Diode

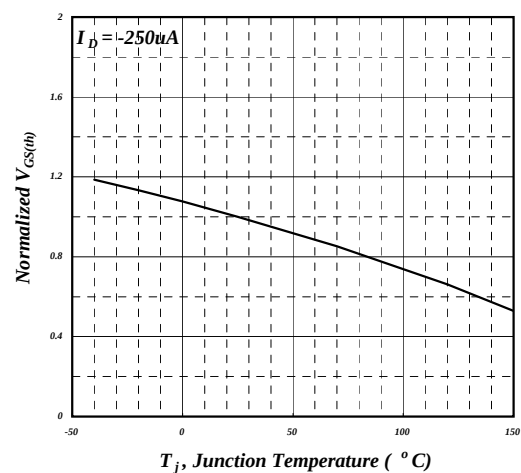


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

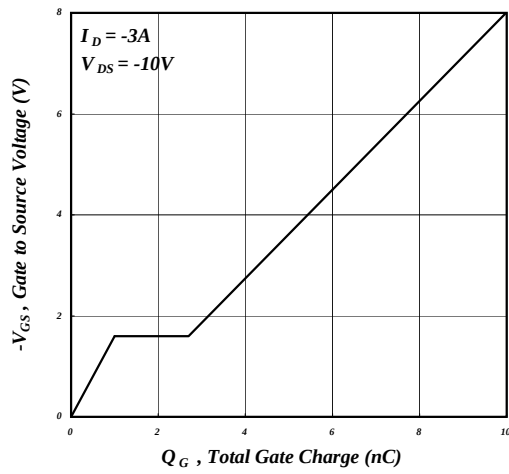


Fig 7. Gate Charge Characteristics

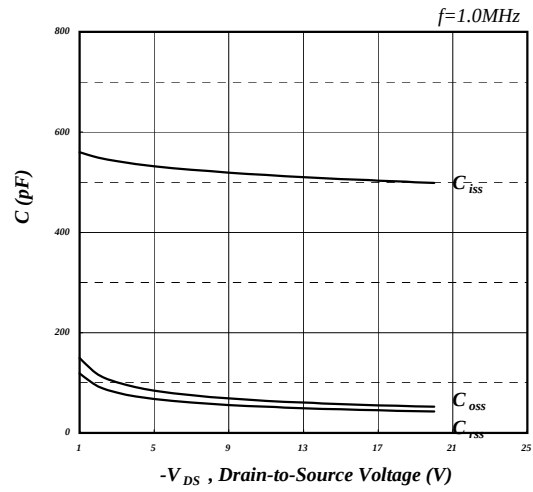


Fig 8. Typical Capacitance Characteristics

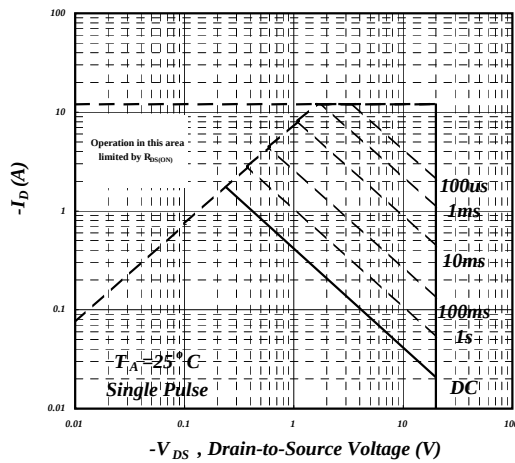


Fig 9. Maximum Safe Operating Area

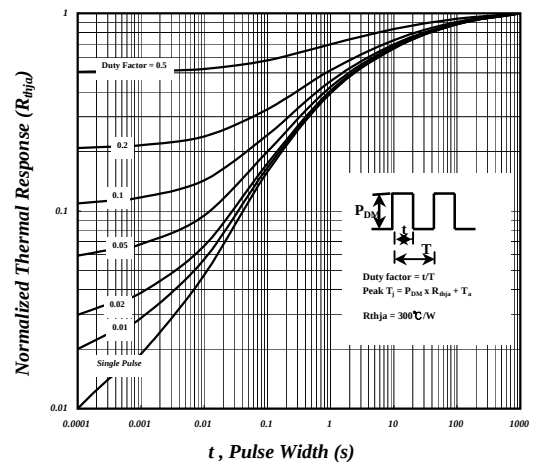


Fig 10. Effective Transient Thermal Impedance

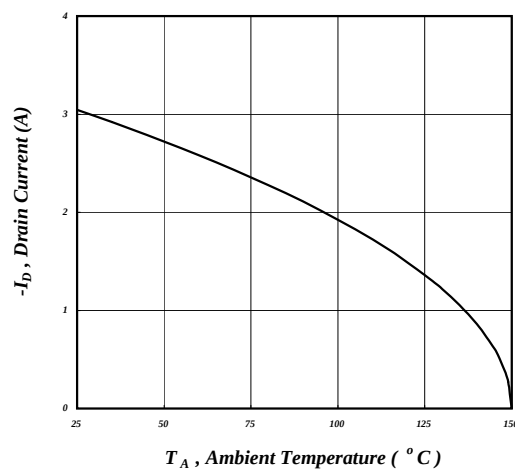


Fig 11. Drain Current v.s. Ambient Temperature

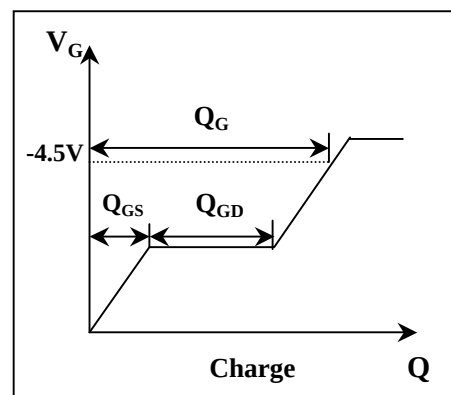
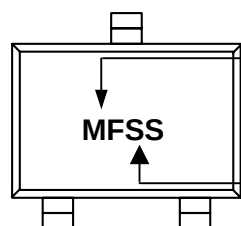


Fig 12. Gate Charge Waveform



MARKING INFORMATION



Part Number : MF

Date Code : SS

SS:2004,2008,2012...

SS:2003,2007,2011...

SS:2002,2006,2010...

SS:2001,2005,2009...